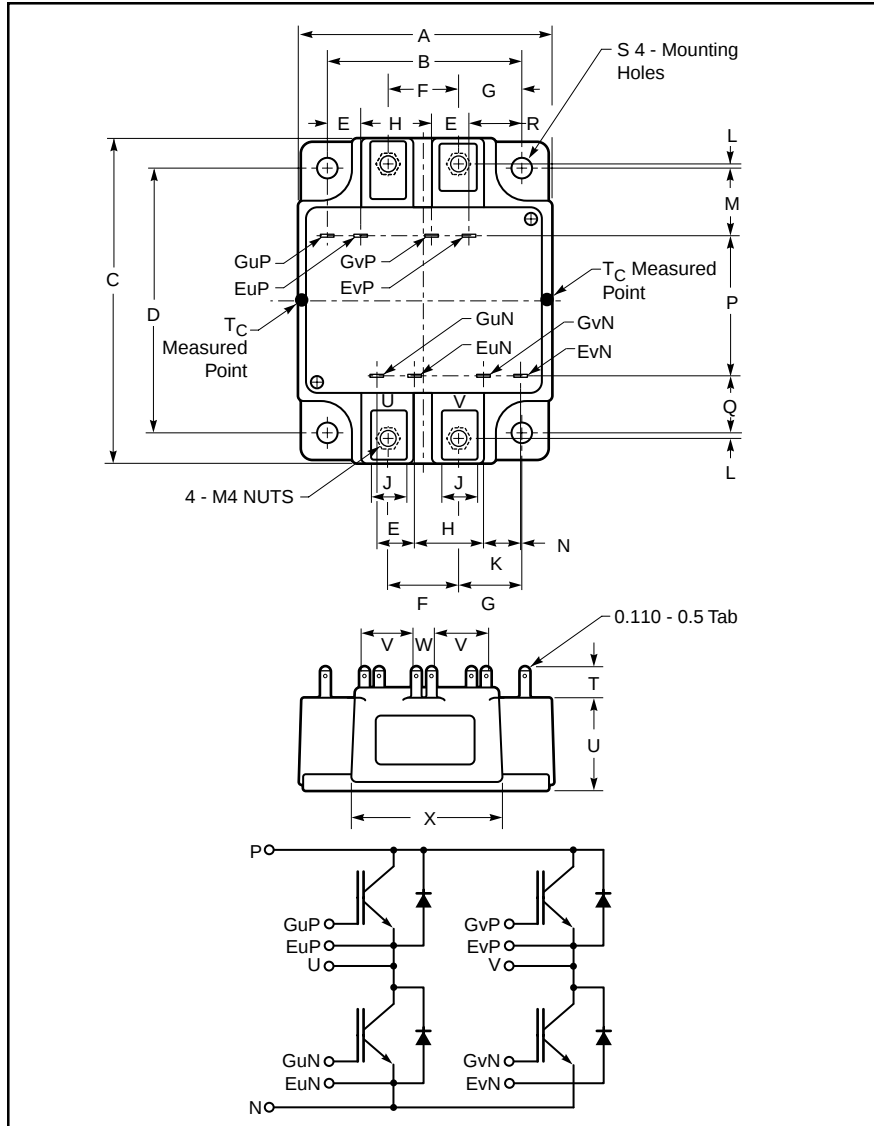


Four IGBTMOD™ U-Series Module 50 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	2.83	72.0
B	2.17±0.01	55±0.25
C	3.58	91.0
D	2.91±0.01	74.0±0.25
E	0.43	11.0
F	0.79	20.0
G	0.69	17.5
H	0.75	19.1
J	0.39	10.0
K	0.41	10.5
L	0.05	1.25

Dimensions	Inches	Millimeters
M	0.74	18.7
N	0.02	0.5
P	1.55	39.3
Q	0.63	16.0
R	0.57	14.4
S	0.22 Dia.	5.5 Dia.
T	0.32	8.1
U	1.02	26.0
V	0.59	15.0
W	0.20	5.0
X	1.61	41.0



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of four IGBT Transistors in an H-Bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery (70ns) Free-Wheel Diode
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM50BU-24H is a 1200V (V_{CES}), 50 Ampere Four-IGBT IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	50	24

CM50BU-24H

Four IGBTMOD™ U-Series Module

50 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM50BU-24H	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_c = 25^\circ\text{C}$)	I_C	50	Amperes
Peak Collector Current ($T_j \leq 150^\circ\text{C}$)	I_{CM}	100*	Amperes
Emitter Current** ($T_c = 25^\circ\text{C}$)	I_E	50	Amperes
Peak Emitter Current**	I_{EM}	100*	Amperes
Maximum Collector Dissipation ($T_c = 25^\circ\text{C}$)	P_C	400	Watts
Mounting Torque, M4 Main Terminal	–	15	in-lb
Mounting Torque, M5 Mounting	–	31	in-lb
Weight	–	390	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	–	–	1	mA
Gate Leakage Voltage	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	–	–	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 5.0\text{mA}, V_{CE} = 10V$	4.5	6	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50A, V_{GE} = 15V, T_j = 25^\circ\text{C}$	–	2.9	3.7	Volts
		$I_C = 50A, V_{GE} = 15V, T_j = 125^\circ\text{C}$	–	2.85	–	Volts
Total Gate Charge	Q_G	$V_{CC} = 600V, I_C = 50A, V_{GE} = 15V$	–	187	–	nC
Emitter-Collector Voltage*	V_{EC}	$I_E = 50A, V_{GE} = 0V$	–	–	3.2	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

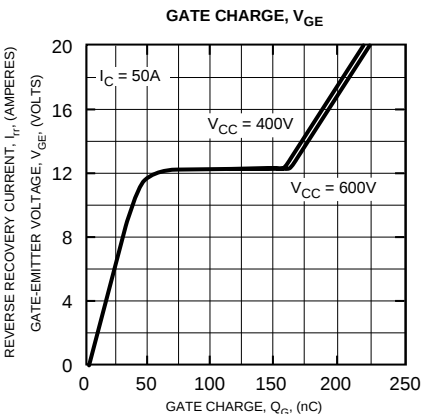
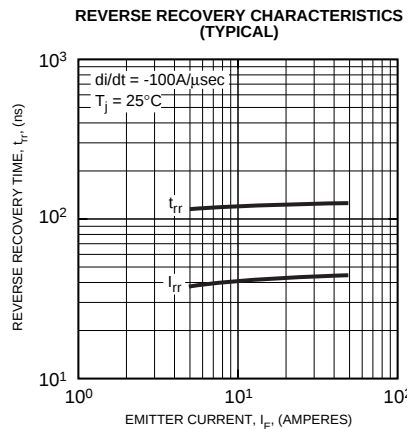
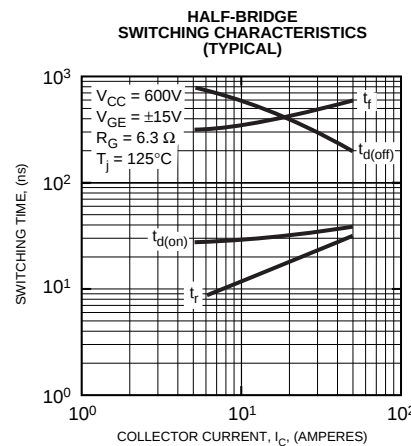
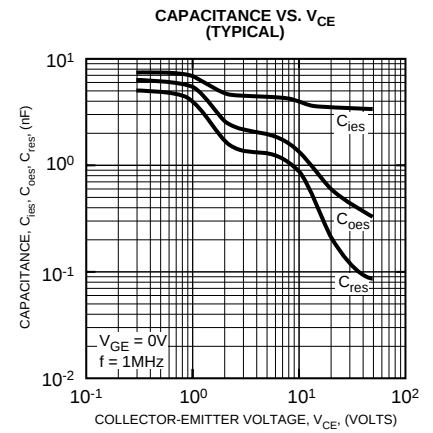
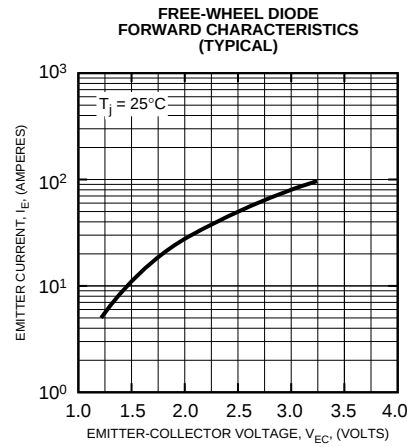
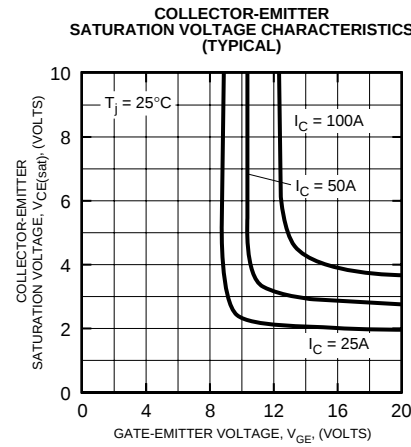
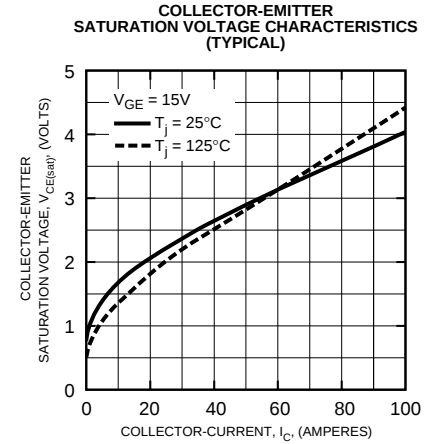
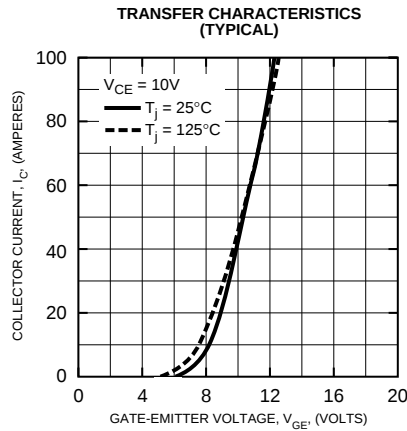
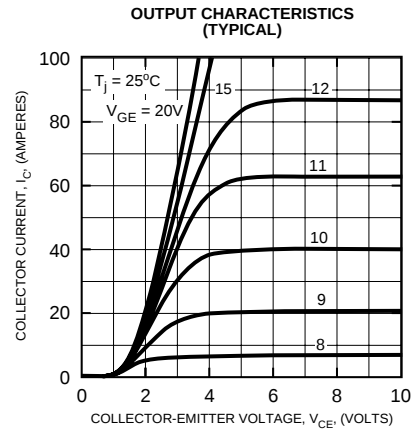
Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0V	–	–	7.5	nf
Output Capacitance		C _{oes}		–	–	2.6	nf
Reverse Transfer Capacitance		C _{res}		–	–	1.5	nf
Resistive	Turn-on Delay Time	t _{d(on)}	V _{CC} = 600V, I _C = 50A,	–	–	80	ns
Load	Rise Time	t _r	V _{GE1} = V _{GE2} = 15V,	–	–	200	ns
Switch	Turn-off Delay Time	t _{d(off)}	R _G = 6.3Ω, Resistive	–	–	150	ns
Times	Fall Time	t _f	Load Switching Operation	–	–	350	ns
Diode Reverse Recovery Time		t _{rr}	I _E = 50A, di _E /dt = -100A/μs	–	–	300	ns
Diode Reverse Recovery Charge		Q _{rr}	I _E = 50A, di _E /dt = -100A/μs	–	0.28	–	μC

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/4 Module	–	–	0.31	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/4 Module	–	–	0.7	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	0.1	–	$^\circ\text{C/W}$

CM50BU-24H
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